

Features

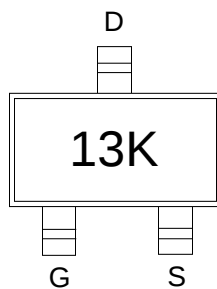
- Trench Power LV MOSFET technology
- High Density Cell Design for Low $R_{DS(ON)}$
- High Speed switching

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
-20V	79mΩ@-4.5V	-3A
	105mΩ@-2.5V	

Application

- Battery protection
- Load switch
- Power management

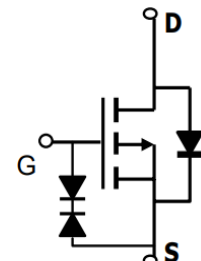


13K: Device code

Marking and pin assignment



SOT-323 top view



Schematic diagram



Pb-Free



RoHS



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	-20	V
V_{GS}	Gate-Source Voltage	±8	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
I_S	Diode Continuous Forward Current	$T_C=25^{\circ}C$ -3	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^{\circ}C$ -14	A
I_D	Continuous Drain Current	$T_C=25^{\circ}C$ -3	A
P_D	Maximum Power Dissipation	$T_C=25^{\circ}C$ 0.5	W
$R_{\theta JA}$	Thermal Resistance Junction-to-Ambient	105	°C/W

Ordering Information (Example)

Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
SSM3J135TU	SOT-323	13K	3,000	45,000	180,000	7" reel

Electrical Characteristics (TJ=25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250μA	-20	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =-20V, V _{GS} =0V	--	--	-1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±8V, V _{DS} =0V	--	--	±10	uA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	--	-1.0	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =-4.5V, I _D =-1.0A	--	79	103	mΩ
		V _{GS} =-2.5V, I _D =-0.6A	--	105	132	mΩ
		V _{GS} =-1.8V, I _D =-0.4A	--	140	180	mΩ
Dynamic Electrical Characteristics @ TJ = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =-15V, V _{GS} =0V, f=1MHz	--	510	--	pF
C _{OSS}	Output Capacitance		--	55	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	16	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =-9V, I _D =-1A, V _{GS} =-4.5V	--	5.5	--	nC
Q _{gs}	Gate Source Charge		--	1.5	--	nC
Q _{gd}	Gate Drain Charge		--	1.25	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-6V, R _L =6Ω, V _{GS} =-4.5V, R _G =6Ω	--	1350	--	nS
t _r	Turn-on Rise Time		--	830	--	nS
t _{d(off)}	Turn-Off Delay Time		--	5500	--	nS
t _f	Turn-Off Fall Time		--	1500	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	TJ=25℃, I _S =-1.4A,	--	--	-1.2	V

Typical Operating Characteristics

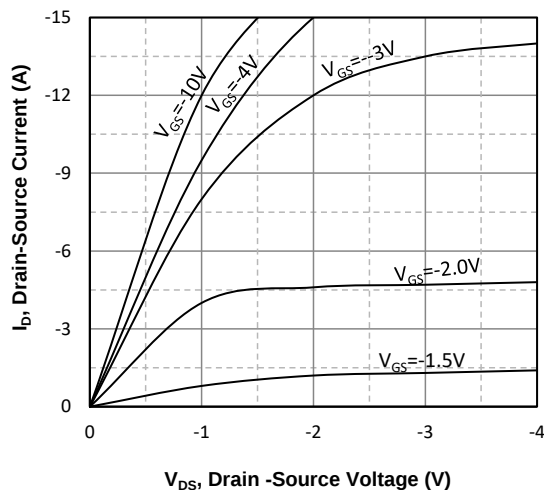


Fig1. Typical Output Characteristics

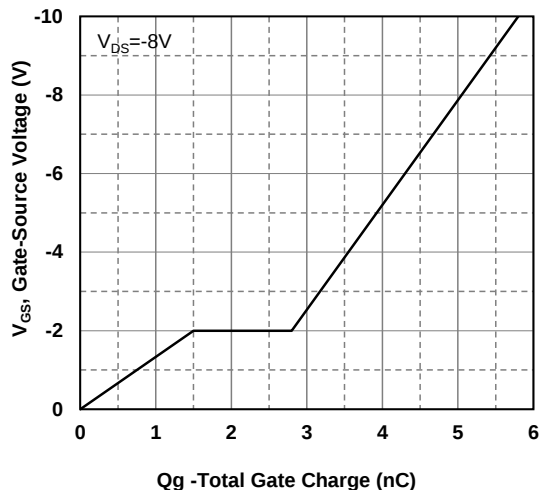


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

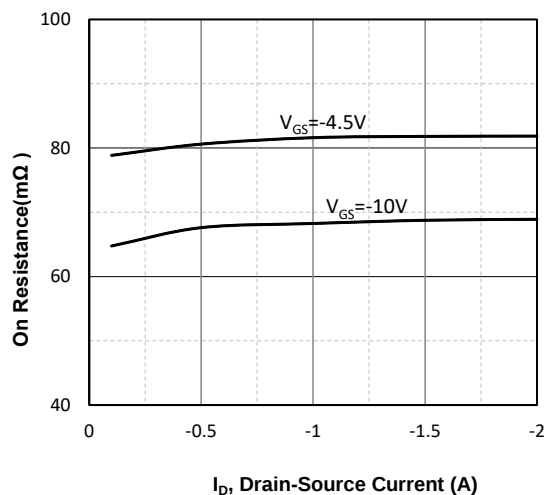


Fig3. Drain-Source on Resistance

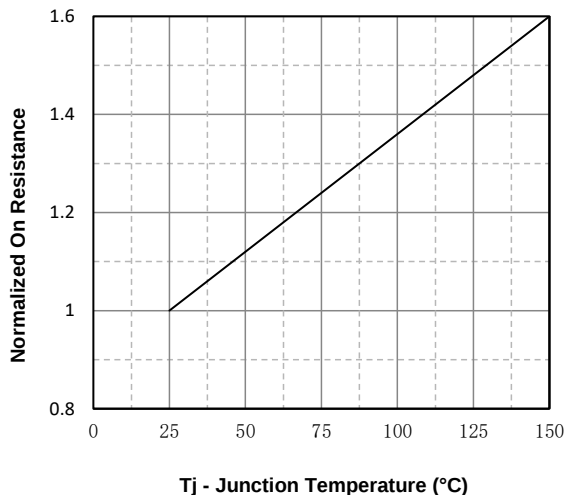


Fig4. Normalized On-Resistance Vs. Temperature

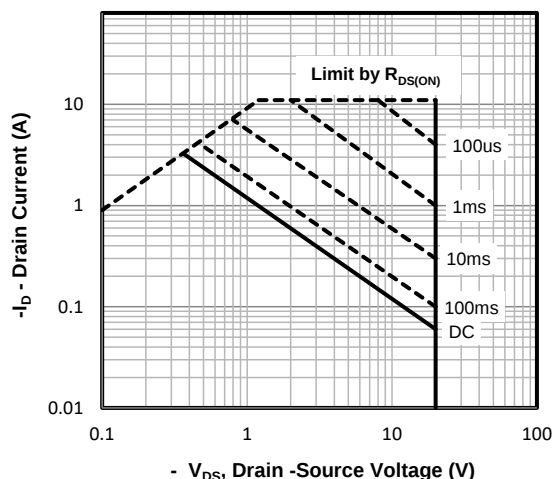


Fig5. Maximum Safe Operating Area

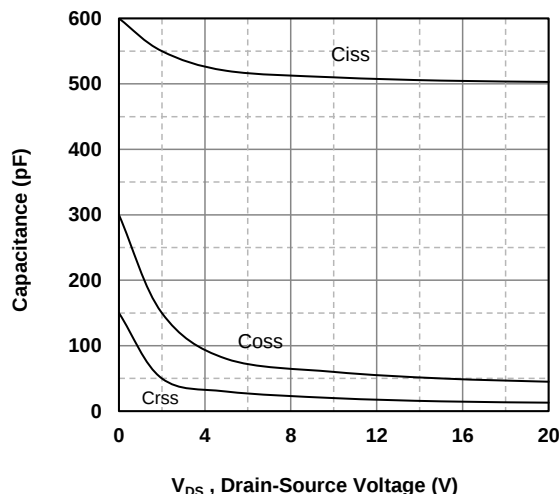
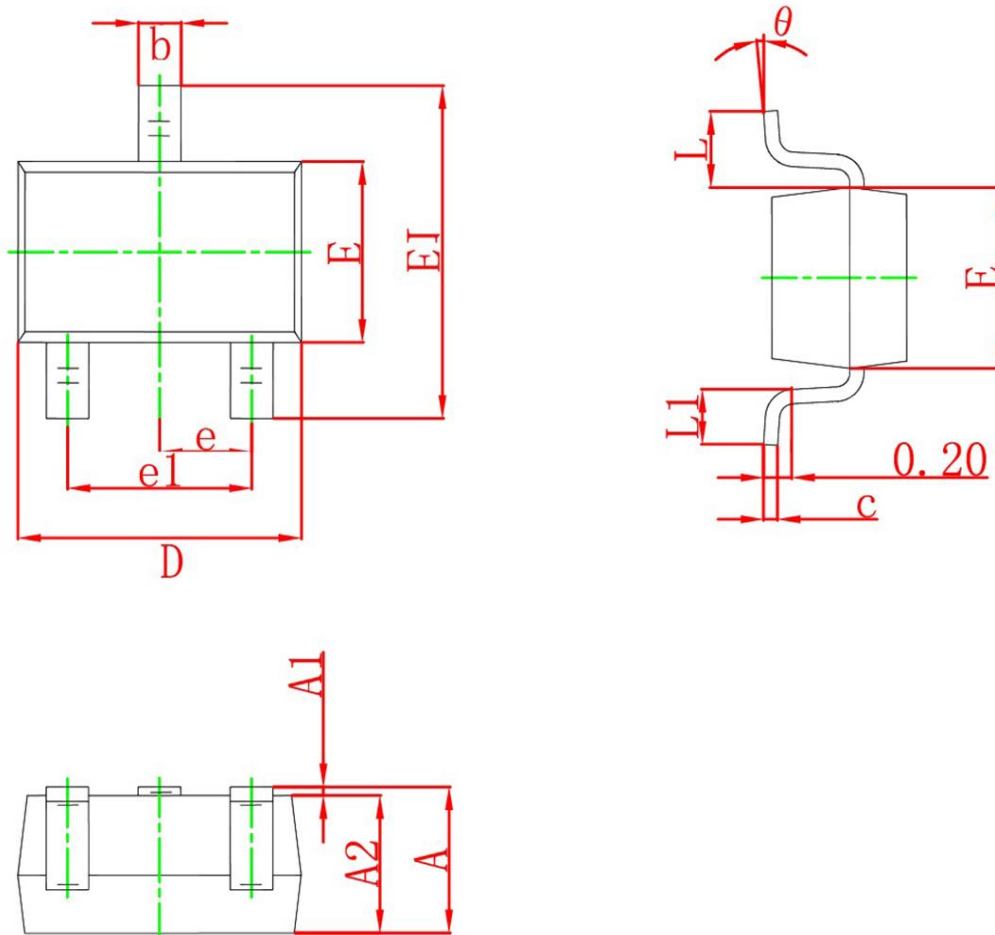


Fig6 Typical Capacitance Vs. Drain-Source Voltage

SOT-323 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650TYP		0.026TYP	
e1	1.200	1.400	0.047	0.055
L	0.525REF		0.021REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°